

EAST - [09880005.wsp:1]

File View Edit Tools Window Help

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     ☒ 1 and semiconductor  
     ☒ L3: (28) 2 and (hole trench film)  
     ☒ L1: (252) electroless-plating adj liquid electroless adj plating ad  
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 1 and semiconductor

	U	1	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1	<input type="checkbox"/>	<input type="checkbox"/>	US 6334802 B1	20020101	21	Electrode for a display device and method for	445/24	
2	<input type="checkbox"/>	<input type="checkbox"/>	US 6201942 B1	20010313	13	Developer-carrying member, and developing device and	399/286	
3	<input type="checkbox"/>	<input type="checkbox"/>	US 6191530 B1	20010220	21	Electrode for a display device and method for	313/586	313/582; 313/584;
4	<input type="checkbox"/>	<input type="checkbox"/>	US 5746927 A	19980505	21	Electrical connecting device and method for making same	216/18	216/20; 216/41;
5	<input type="checkbox"/>	<input type="checkbox"/>	US 5615030 A	19970325	23	Black matrix substrate, and color filter and liquid	349/110	430/7
6	<input type="checkbox"/>	<input type="checkbox"/>	US 5610371 A	19970311	21	Electrical connecting device and method for making same	174/262	174/257; 361/760;
7	<input type="checkbox"/>	<input type="checkbox"/>	US 5603981 A	19970218	8	Electrical connecting device and method for making same	427/96	228/180.21; 29/830;
8	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5501900 A	19960326	23	Black matrix substrate, and color filter and liquid	428/323	428/1.6; 428/195;
9	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5440454 A	19950808	8	Electrical connecting device and method for making same	361/790	174/260; 174/261;
10	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5342806 A	19940830	18	Method for fabricating a semiconductor device having	438/608	438/625; 438/642;
11	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5332697 A	19940726	5	Formation of silicon nitride by nitridation of porous	438/479	423/344; 438/49;

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